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CLAIMS

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1. A method of manufacturing an electronic device, said method comprising the steps of:

forming a first conductive portion possessor comprising a first conductive portion and a second conductive portion, said first conductive portion containing a

5 first metal or metal compound having a first equilibrium electrode potential, said second conductive portion being electrically connected to said first conductive portion and containing a second metal or metal compound having a second equilibrium electrode potential, said first and second conductive portions being exposed from a surface of said first conductive portion possessor;

10 forming a coating film on said surface of said first conductive portion possessor;

forming a photosensitive film on said first conductive portion possessor on which said coating film has been formed;

15 exposing said photosensitive film to light in a predetermined exposure pattern; and

developing said exposed photosensitive film.

2. A method of manufacturing an electronic device as claimed in claim 1, wherein said step of forming said first conductive portion possessor comprises the
20 step of forming said first and second conductive portions on a supporting member in such a way that said second conductive portion lies on the top of said first conductive portion.

3. A method of manufacturing an electronic device as claimed in claim 2,
25 wherein said step of forming said first conductive portion possessor comprises the step of forming an insulating film on said supporting member before said step of forming said first and second conductive portions.

4. A method of manufacturing an electronic device as claimed in claim 1,
30 wherein said step of forming said first conductive portion possessor comprises the step of forming said first and second conductive portions in such a way that said first conductive portion is electrically connected to said second conductive portion through a hole of an insulating film.

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| 5. A method of manufacturing an electronic device as claimed in claim 3, wherein said step of forming said insulating film is the step of forming an insulating film having silicon nitride or silicon dioxide,

5 and wherein said step of forming said coating film is the step of forming a coating film containing chromium molybdenum oxide.

6. A method of manufacturing an electronic device, said method comprising the steps of:

10 forming a second conductive portion possessor comprising a first conductive portion and a second conductive portion, said first conductive portion containing a first metal or metal compound having a first equilibrium electrode potential, said second conductive portion being electrically connected to said first conductive portion and containing a second metal or metal compound having a second equilibrium electrode potential, said first and second conductive portions being exposed from a surface of said second conductive portion possessor;

15 forming a photosensitive film on said surface of said second conductive portion possessor;

exposing said photosensitive film to light in a predetermined exposure pattern; and

20 developing said exposed photosensitive film;

wherein said step of forming said second conductive portion possessor is the step of forming said second conductive portion possessor comprising a sacrificial electrode, said sacrificial electrode being electrically connected to said first and second conductive portions, said sacrificial electrode being exposed from said 25 surface of said second conductive portion possessor.

7. A method of manufacturing an electronic device as claimed in claim 6, said sacrificial electrode is directly connected to one of said first and second conductive portions

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8. A method of manufacturing an electronic device as claimed in claim 6, said sacrificial electrode and one of said first and second conductive portions are integrally formed.

35 9. A method of manufacturing an electronic device as claimed in any one of claims 6 to 8, wherein said step of forming said second conductive portion possessor comprises the step of forming said first and second conductive portions in such a way that said second conductive portion lies on the top of said first conductive portion.

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10. A method of manufacturing an electronic device as claimed in any one of claims 6 to 8, wherein said step of forming said second conductive portion possessor comprises the step of forming said first and second conductive portions in such a way that said first conductive portion is electrically connected to said second 5 conductive portion through a hole of an insulating film.

11. A method of manufacturing an electronic device, said method comprising the steps of:

10 forming a third conductive portion possessor comprising a first conductive portion and a conductive film, said first conductive portion containing a first metal or metal compound having a first equilibrium electrode potential, said conductive film being electrically connected to said first conductive portion and containing a second metal or metal compound having a second equilibrium electrode potential, said conductive film being exposed from a surface of said third conductive portion 15 possessor; and

wet-etching said conductive film in such a way that a second conductive portion is formed, said second conductive portion being electrically connected to said first conductive portion and containing said second metal or metal compound;

20 wherein in said wet-etching step, said conductive film is wet-etched in such a way that not only said second conductive portion but also a sacrificial electrode are formed, said sacrificial electrode being electrically connected to said first conductive portion.

12. A method of manufacturing an electronic device as claimed in claim 11, 25 wherein said conductive film is formed so as to cover said first conductive portion, and wherein in said wet-etching step, said conductive film is wet-etched in such a way that at least part of said first conductive portion is exposed.

13. A method of manufacturing an electronic device as claimed in claim 11 or 12, 30 comprising a step of removing a part of said first conductive portion after said wet-etching step.

14. An electronic device comprising:

35 a first base comprising a first conductive portion and a second conductive portion, said first conductive portion containing a first metal or metal compound having a first equilibrium electrode potential, said second conductive portion being electrically connected to said first conductive portion and containing a second metal or metal compound having a second equilibrium electrode potential; an underlying layer formed on said first base; and

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a reflective portion formed on a surface of said underlying layer, said reflective portion comprising a plurality of projections or recesses; wherein said underlying layer comprises:

5 coating portions provided at positions corresponding to said plurality of projections or recesses; and

an underlying layer main portion formed using photosensitive material, said underlying layer main portion covering said coating portions.

15. An electronic device as claimed in claim 14, wherein said first base
10 comprises:

 a supporting member;

 said first conductive portion formed on said supporting member; and

 said second conductive portion formed so as to lie on said first conductive portion.

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16. An electronic device as claimed in claim 15, wherein said first conductive portion is formed on an insulating film.

17. An electronic device as claimed in claim 14, wherein said first base
20 comprises:

 a supporting member;

 said first conductive portion formed on said supporting member;

 an insulating film having a hole for electrically connecting said first and second conductive portions; and

25 said second conductive portion electrically connected to said first conductive portion through said hole.

18. An electronic device as claimed in claim 16 or 17, wherein said insulating film has silicon nitride or silicon dioxide, and wherein said coating portion has
30 chromium molybdenum oxide.

19. An electronic device comprising:

 a first conductive portion containing a first metal or metal compound having
35 a first equilibrium electrode potential,

 a second conductive portion containing a second metal or metal compound having a second equilibrium electrode potential, said second conductive portion being electrically connected to said first conductive portion and;

 a sacrificial electrode electrically connected to said first and second conductive portions.

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20. An electronic device as claimed in claim 19, said sacrificial electrode is directly connected to one of said first and second conductive portions.
- 5 21. An electronic device as claimed in claim 19, said sacrificial electrode and one of said first and second conductive portions are integrally formed.
22. An electronic device as claimed in any one of claims 19 to 21, wherein said sacrificial electrode contains said first or second metal or metal compound.
- 10 23. An electronic device as claimed in any one of claims 19 to 22, wherein said second conductive portion lies on the top of said first conductive portion.
- 15 24. An electronic device as claimed in claim 15, 16 or 23, wherein a combination of said first and second conductive portions forms at least part of a gate electrode, a gate bus, a source electrode or a source bus.
- 20 25. An electronic device as claimed in claim 24, wherein said first conductive portion has molybdenum as said first metal or metal compound, and wherein said second conductive portion has aluminum as said second metal or metal compound.
26. An electronic device as claimed in any one of claims 19 to 22, wherein said first conductive portion is electrically connected to said second conductive portion via a hole of an insulating film.
- 25 27. An electronic device as claimed in 15, 16 or 26, wherein said first conductive portion is at least part of a gate terminal, and wherein said second conductive portion is at least part of a gate bus.
- 30 28. An electronic device as claimed in 15, 16 or 26, wherein said first conductive portion is at least part of a source terminal, and wherein said second conductive portion is at least part of a gate electrode of an ESD transistor.
- 35 29. An electronic device as claimed in claim 27 or 28, wherein said first conductive portion has indium oxide as said first metal or metal compound, and wherein said second conductive portion has aluminum or molybdenum as said second metal or metal compound.
- 30 30. An electronic device as claimed in claim 19, wherein said electronic device comprises a third conductive portion, and wherein said first conductive portion covers a part of said third conductive portion.

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31. An electronic device as claimed in claim 30, wherein said third conductive portion is at least part of a gate terminal.

5 32. An image display device comprising an electronic device as claimed in any one of claims 14 to 31.

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